WHAT IS CLAIMED IS:

1. A heater divided into a plurality of control zones, the heater comprising:

a parallel circuit installed for a control zone, which is located in a wafer region, among the control zones; and

a plurality of heat generators installed for the control zone that is located in the wafer region, wired in parallel in the parallel circuit, and configured to raise an internal temperature of a reaction tube by heat generation,

wherein the parallel circuit is configured to be capable of adjusting a power outputted from at least one of the plurality of heat generators by connecting at least one output variable element to the at least one of the plurality of heat generators to thereby adjust a power supplied to the at least one of the plurality of heat generators.

2. The heater according to Claim 1, wherein the parallel circuit includes two or more parallel wirings in the control zone located in the substrate region.

3. The heater according to Claim 1, wherein the parallel circuit is a resistance circuit.

4. The heater according to Claim 1, wherein the output variable element is at least one selected from the group of a resistor, a thyristor, and an IGBT.

5. A temperature control system, comprising:

a heater divided into a plurality of control zones, the heater including:

a parallel circuit installed for a control zone, which is located in a wafer region, among the control zones; and

a plurality of heat generators installed for the control zone that is located in the wafer region, wired in parallel in the parallel circuit, and configured to raise an internal temperature of a reaction tube by heat generation, wherein the parallel circuit is configured to be capable of

adjusting a power outputted from at least one of the plurality of heat generators by connecting at least one output variable element to the at least one of the plurality of heat generators to thereby adjust a power supplied to the at least one of the plurality of heat generators; and

a temperature controller configured to control the heater by regulating electric power supplied to the heat generators based on temperatures detected by detectors installed at the heat generators.

6. The system according to Claim 5, wherein the temperature controller is further configured to output different electric power for each of the control zones.

7. The system according to Claim 5, further comprising an adjuster configured to adjust electric power outputted from a circuit to which the output variable element is connected,

wherein the adjuster is configured to be capable of outputting different electric power for each circuit constituting the parallel circuit.

8. The system according to Claim 7, further comprising a temperature control calculator configured to perform temperature control calculation such that a temperature detected by a temperature detector matches a preset temperature,

wherein the adjuster is configured to determine an output to the circuit constituting the parallel circuit based on a ratio of control signal calculated by the temperature control calculator.

9. A processing apparatus, at least comprising:

a heater divided into a plurality of control zones, the heater including:

a parallel circuit installed for a control zone, which is located in a wafer region, among the control zones; and

a plurality of heat generators installed for the control zone that is

located in the wafer region, wired in parallel in the parallel circuit, and configured to raise an internal temperature of a reaction tube by heat generation,

wherein the parallel circuit is configured to be capable of adjusting a power outputted from at least one of the plurality of heat generators by connecting at least one output variable element to the at least one of the plurality of heat generators to thereby adjust a power supplied to the at least one of the plurality of heat generators.

10. The processing apparatus according to Claim 9, wherein the heater is configured to output different electrical power in a vertical direction of the control zone located in the substrate region

11. The processing apparatus according to Claim 9, wherein the heater is configured to output different electrical power for each circuit constituting the parallel circuit.

12. The processing apparatus according to Claim 9, wherein the heater is configured to output electrical power according to a resistance value of each circuit constituting the parallel circuit

13. The processing apparatus according to Claim 9, wherein the heater is configured such that electrical power outputted to a circuit in which the output variable element is not installed is larger than electrical power outputted to a circuit to which the output variable element is connected.

14. The processing apparatus according to Claim 9, wherein the output variable element is at least one selected from the group of a resistor, a thyristor, and an IGBT.

15. The processing apparatus according to Claim 9, wherein the at least one output

variable element includes a plurality of output variable elements, and

wherein the processing apparatus comprises a controller configured to input control signals, which are different from each other, to the plurality of output variable elements.

16. The processing apparatus according to Claim 9, wherein the output variable element is installed for each circuit constituting the parallel circuit, and

wherein the processing apparatus is configured such that electrical power outputted from each output variable element is capable of being regulated according to a parameter.

17. The processing apparatus according to Claim 16, wherein the parameter is changeable according to a preset temperature.

18. The processing apparatus according to Claim 16, wherein the at least one output variable element includes a plurality of output variable elements, and

wherein the processing apparatus comprises a controller configured to input control signals, which are the same as each other, to the plurality of output variable elements.

19. A method of manufacturing a semiconductor device, comprising

processing a substrate disposed in a reaction tube by heating the substrate by a heater divided into a plurality of control zones, the heater including:

a parallel circuit installed for a control zone, which is located in a wafer region, among the control zones; and

a plurality of heat generators installed for the control zone that is located in the wafer region, wired in parallel in the parallel circuit, and configured to raise the internal temperature of the reaction tube by heat generation,

wherein the parallel circuit is configured to be capable of adjusting a power outputted from at least one of the plurality of heat generators by connecting at least one output variable element to the at least one of the plurality of heat generators to thereby adjust a power supplied to the at least one of the plurality of heat generators.